



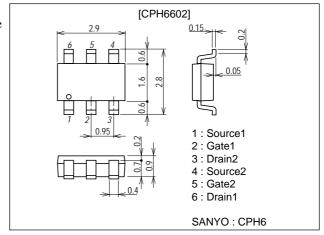
# **Ultrahigh-Speed Switching Applications**

#### **Features**

- · Low ON-resistance.
- · Ultrahigh-speed switching.
- · 2.5V drive.
- Composite type with 2 MOSFETs contained in a single package, facilitating high-density mounting.

# **Package Dimensions**

unit : mm 2202



# **Specifications**

#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		20	V
Gate-to-Source Voltage	VGSS		±10	V
Drain Current (DC)	ΙD		2.0	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	8.0	Α
Allowable Power Dissipation	PD	Mounted on a ceramic board (900mm <sup>2</sup> X0.8mm)1unit	0.9	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

#### Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Oill
Drain-to-Source Breakdown Voltage	V(BR)DSS	I <sub>D</sub> =1mA, V <sub>GS</sub> =0	20			V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =20V, V <sub>GS</sub> =0			1	μΑ
Gate-to-Source Leakage Current	IGSS	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0			±10	μΑ
Cutoff Voltage	VGS(off)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	0.4		1.3	V
Forward Transfer Admittance	yfs	V <sub>DS</sub> =10V, I <sub>D</sub> =1A	2.4	3.5		S
Static Drain-to-Source On-State Resistance	R <sub>DS</sub> (on)1	I <sub>D</sub> =1A, V <sub>GS</sub> =4V		100	130	mΩ
	R <sub>DS</sub> (on)2	I <sub>D</sub> =0.5A, V <sub>GS</sub> =2.5V		130	180	mΩ

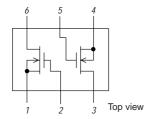
Marking: FM Continued on next page.

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Parameter	Symbol	Conditions	Ratings			Unit
	Symbol		min	typ	max	Uill
Input Capacitance	Ciss	V <sub>DS</sub> =10V, f=1MHz		190		pF
Output Capacitance	Coss	V <sub>DS</sub> =10V, f=1MHz		40		pF
Reverse Transfer Capacitance	Crss	V <sub>DS</sub> =10V, f=1MHz		25		pF
Turn-ON Delay Time	t <sub>d</sub> (on)	See specified Test Circuit.		9		ns
Rise Time	t <sub>r</sub>	See specified Test Circuit.		25		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit.		25		ns
Fall Time	tf	See specified Test Circuit.		18		ns
Total Gate Charge	Qg	V <sub>DS</sub> =10V, V <sub>GS</sub> =4V, I <sub>D</sub> =2A		2.7		nC
Gate-to-Source Charge	Qgs	V <sub>DS</sub> =10V, V <sub>GS</sub> =4V, I <sub>D</sub> =2A		0.6		nC
Gate-to-Drain "Miller" Charge	Qgd	V <sub>DS</sub> =10V, V <sub>GS</sub> =4V, I <sub>D</sub> =2A		0.6		nC
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =2A, V <sub>GS</sub> =0		0.87	1.2	V

#### **Electrical Connection**



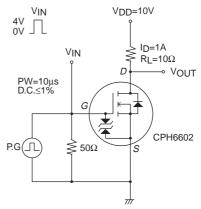
1 : Source1 2 : Gate1

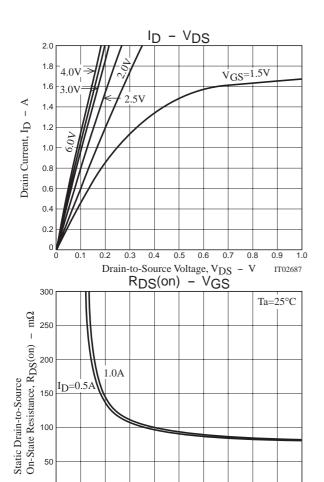
3: Drain2

5 : Gate2 6 : Drain1

4 : Source2

# **Switching Time Test Circuit**

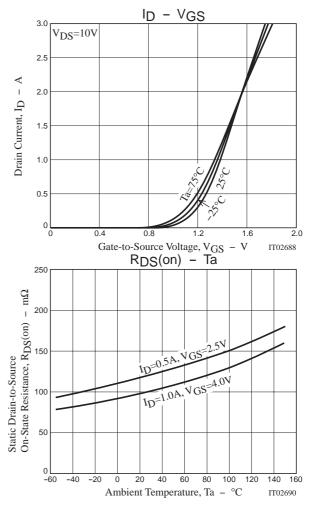




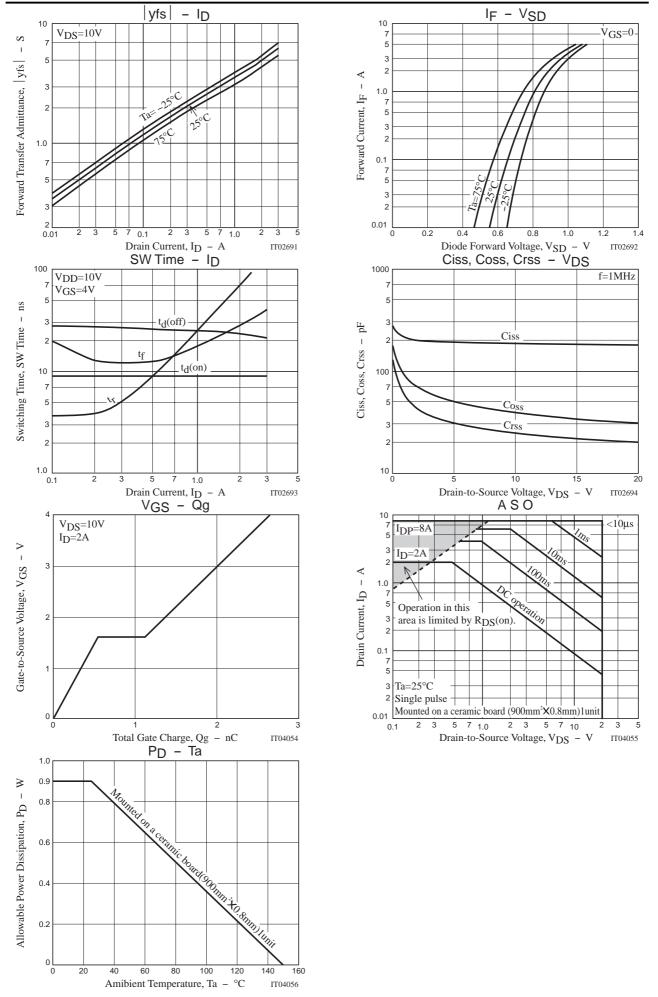
5

Gate-to-Source Voltage,  $V_{GS} - V$ 

10



# **CPH6602**



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